

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the applications. Please amend claims 18 and 33 as shown below, all without prejudice.

Listing of Claims:

Claims 1-17: Cancelled

18.(Currently Amended) A memory system ~~system~~ comprising:

a plurality of memory groups, each of said memory groups comprising a plurality of memory sectors, each of said memory sectors comprising a plurality of memory cells, wherein the number of memory sectors in each memory group is configurable;

a plurality of group tags, each of said group tags corresponds to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are erasable; and

a plurality of sector tags, each of said sector tags corresponds to a memory sector, each of said sector tags indicating whether the memory cells under the corresponding memory sector are erasable,

wherein all the memory cells belonging to one memory sector are erasable when either the corresponding sector tag or the corresponding group tag of the memory sector is set;

wherein any combination of memory sectors in a memory group can be simultaneously erased, and any combination of the memory groups can be simultaneously erased.

19.(Original) The memory system according to Claim 18, wherein the corresponding sectors in each memory group is calculated in real time.

Claims 20 and 21: Cancelled

22.(Previously Presented) The memory system according to claim 18, wherein said memory system is a flash memory.

Claim 23: Cancelled

24.(Previously Presented) A memory system comprising:

a plurality of memory groups, each of said memory groups comprising a plurality of memory cells, wherein the number of memory cells in each memory group is configurable;

a plurality of group tags, each of said group tags corresponding to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are write protected; and

wherein any combination of the memory groups can be write protected.

25.(Previously Presented) A memory system comprising:

a plurality of memory groups, each of said memory groups comprising a plurality of memory cells, wherein the corresponding cells in each memory group are calculated in real time;

a plurality of group tags, each of said group tags corresponding to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are write protected; and

wherein any combination of the memory groups can be write protected.

26.(Previously Presented) The memory system according to claim 24 is a flash memory.

27.(Previously Presented) The memory system according to claim 25 is a flash memory.

28.(Previously Presented) The memory system according to claim 18, wherein said sector tags and said group tags are settable by a host to which the memory system is connected.

29.(Previously Presented) The memory system according to Claim 28, wherein said sector tags and said group tags are set in response to a host command.

30.(Previously Presented) The memory system according to Claim 29, wherein set ones of said sector tags and said group tags are deselected in response to a host command.

31.(Previously Presented) The memory system according to Claim 18, wherein the number of memory sectors in each memory group is configurable by a host to which the memory system is connected.

Claim 32: Cancelled

33.(Currently Amended) ~~The A~~ memory system according to claim 18, comprising:
a plurality of memory groups, each of said memory groups comprising a plurality of memory sectors, each of said memory sectors comprising a plurality of memory cells,
wherein the number of memory sectors in each memory group is configurable;

a plurality of group tags, each of said group tags corresponds to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are erasable; and

a plurality of sector tags, each of said sector tags corresponds to a memory sector, each of said sector tags indicating whether the memory cells under the corresponding memory sector are erasable,

wherein all the memory cells belonging to one memory sector are erasable when either the corresponding sector tag or the corresponding group tag of the memory sector is set;

wherein any combination of memory sectors in a memory group can be simultaneously erased, and any combination of the memory groups can be simultaneously erased; and

wherein in response to too few tags being set, a received erase command is aborted.

34.(Previously Presented) The memory system according to claim 24, wherein said group tags are settable by a host to which the memory system is connected.

35.(Previously Presented) The memory system according to Claim 34, wherein said group tags are set in response to a host command.

36.(Previously Presented) The memory system according to Claim 35, wherein set ones of said group tags are deselected in response to a host command.

37.(Previously Presented) A memory system comprising:
a plurality of memory groups, each of said memory groups comprising a plurality of memory cells;
a plurality of group tags, each of said group tags corresponding to one of said memory groups, each of said group tags indicating whether the memory cells under the corresponding memory group are write protected; and
wherein any combination of the memory groups can be write protected and said group tags are settable in response to a command from a host to which the memory system is connected.

38.(Previously Presented) The memory system according to Claim 37, wherein set ones of said group tags are deselected in response to command from said host.

39.(Previously Presented) A method of operating a memory card that includes a memory array formed of a plurality of units of erase, each which is composed of a plurality of memory cells, the method comprising:

organizing the memory into a plurality of memory groups, each of said memory groups comprising a plurality of units of erase,

wherein all the memory cells belonging to one of said units of erase memory sector are erasable when either the corresponding unit of erase or the corresponding group of the units of erase is selected, and

wherein any combination of units of erase in a memory group can be simultaneously erased, and any combination of the memory groups can be simultaneously erased.

40.(Previously Presented) The method of claim 39, wherein the size of the groups is configurable by a host to which the card is connected.

41.(Previously Presented) The method of claim 40, wherein the size of the groups is stored in a register on card.